

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A multiple exposure mask pattern for multiple exposures for forming a resist pattern with an unvarying pattern pitch on a semiconductor wafer, which is utilized instead of as in case where a one exposure mask pattern under a design having ~~[[the]]~~ a width of an aperture pattern of the one exposure mask smaller than ~~[[the]]~~ a width of a light-shielding pattern ~~is used at one exposure of the one exposure mask~~, wherein the multiple exposure mask pattern for multiple exposures comprises an aperture pattern and a light-shielding pattern with apertures between light-shielding portions, where the multiple exposure mask pattern has a pattern pitch that is the same as that of the one exposure mask pattern under design and has ~~a the~~ width of ~~[[an]]~~ the aperture pattern of the multiple exposure mask pattern that is greater than ~~[[the]]~~ a width of ~~[[a]]~~ the light-shielding pattern of the multiple exposure mask pattern.

2. (Currently amended) The mask pattern according to claim 1, wherein the multiple exposure mask pattern is formed of chrome.

3. (Currently amended) The mask pattern according to claim 1, wherein the multiple exposure mask pattern is formed of silicon.

4. (Currently amended) The mask pattern according to claim 1, wherein the aperture pattern of the multiple exposure mask pattern is formed using a halftone mask that becomes a phase shifter.

5. (Currently amended) The mask pattern according to claim 1, wherein the aperture pattern of the multiple exposure mask pattern is formed using a Levenson mask that becomes a phase shifter.

6. (Currently amended) The mask pattern according to claim 1, wherein the light-shielding pattern of the multiple exposure mask pattern is formed by using a binary mask made of chrome.

7. (Currently amended) The mask pattern according to claim 1, wherein the light-shielding pattern of the multiple exposure mask pattern is formed by using a halftone mask made of MoSiO.

8. (Canceled)